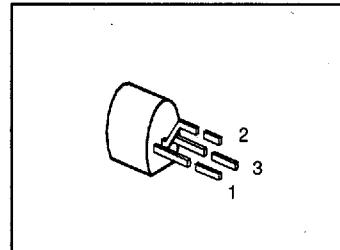


PNP Silicon AF Transistors

BCX 78
BCX 79

- High current gain
- Low collector-emitter saturation voltage
- Low noise at 1 kHz
- Low noise at low frequencies
- Complementary types: BCX 58, BCX 59 (NPN)



Type	Marking	Ordering Code	Pin Configuration			Package ¹⁾
			1	2	3	
BCX 78	-	Q62702-C717	C	B	E	TO-92
BCX 78-VII		Q62702-C626				
BCX 78-VIII		Q62702-C627				
BCX 78-IX		Q62702-C628				
BCX 78-X		Q62702-C629				
BCX 79		Q62702-C718				
BCX 79-VII		Q62702-C630				
BCX 79-VIII		Q62702-C631				
BCX 79-IX		Q62702-C632				
BCX 79-X		Q62702-C633				

¹⁾ For detailed information see chapter Package Outlines.

Maximum Ratings

Parameter	Symbol	Values		Unit
		BCX 78	BCX 79	
Collector-emitter voltage	V_{CE0}	32	45	V
Collector-base voltage	V_{CB0}	32	45	
Emitter-base voltage	V_{EB0}		5	
Collector current	I_C		100	mA
Peak collector current	I_{CM}		200	
Peak base current	I_{BM}		200	
Total power dissipation, $T_c = 70\text{ }^\circ\text{C}$	P_{tot}		500	mW
Junction temperature	T_j		150	$^\circ\text{C}$
Storage temperature range	T_{stg}	- 65 ... + 150		

Thermal Resistance

Junction - ambient	R_{thJA}	≤ 250	K/W
Junction - case ¹⁾	R_{thJC}	≤ 160	

¹⁾ Mounted on Al heat sink 15 mm × 25 mm × 0.5 mm.

Electrical Characteristicsat $T_A = 25^\circ\text{C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

DC characteristics

Collector-emitter breakdown voltage $I_C = 2 \text{ mA}$	$V_{(\text{BR})\text{CEO}}$	32 45	— —	— —	V
Collector-base breakdown voltage $I_C = 10 \mu\text{A}$	$V_{(\text{BR})\text{CBO}}$	32 45	— —	— —	
Emitter-base breakdown voltage $I_E = 1 \mu\text{A}$	$V_{(\text{BR})\text{EBO}}$	5	—	—	
Collector cutoff current $V_{CB} = 32 \text{ V}$	I_{CBO}	—	—	20	nA
$V_{CB} = 45 \text{ V}$		—	—	20	nA
$V_{CB} = 32 \text{ V}, T_A = 150^\circ\text{C}$		—	—	10	μA
$V_{CB} = 45 \text{ V}, T_A = 150^\circ\text{C}$		—	—	10	μA
Collector cutoff current $V_{CB} = 32 \text{ V}, V_{BE} = 0.2 \text{ V}, T_A = 100^\circ\text{C}$	I_{CEO}	—	—	20	μA
$V_{CB} = 45 \text{ V}, V_{BE} = 0.2 \text{ V}, T_A = 100^\circ\text{C}$		—	—	20	
Emitter cutoff current $V_{EB} = 4 \text{ V}$	I_{EBO}	—	—	20	nA
DC current gain $I_C = 10 \mu\text{A}, V_{CE} = 5 \text{ V}$	h_{FE}	20 30 40 100	140 200 270 340	— — — —	—
$I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}$		120 180 250 380	170 250 350 500	220 310 460 630	
$I_C = 100 \text{ mA}, V_{CE} = 1 \text{ V}^1)$		40 45 60 60	— — — —	— — — —	

¹⁾ Pulse test: $t \leq 300 \mu\text{s}$, $D \leq 2 \%$.

Electrical Characteristicsat $T_A = 25^\circ\text{C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

DC characteristics

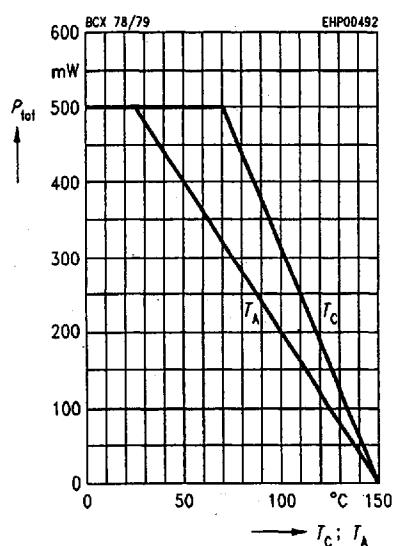
Collector-emitter saturation voltage ¹⁾ $I_C = 100 \text{ mA}, I_B = 2.5 \text{ mA}$	V_{CEsat}	—	—	0.6	V
Base-emitter saturation voltage ¹⁾ $I_C = 100 \text{ mA}, I_B = 2.5 \text{ mA}$	V_{BEsat}	—	—	1.0	
Base-emitter voltage $I_C = 10 \mu\text{A}, V_{CE} = 5 \text{ V}$ $I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}$ $I_C = 100 \text{ mA}, V_{CE} = 1 \text{ V}$ ¹⁾	$V_{BE(on)}$	— 0.55 —	0.52 0.65 0.93	— 0.75 —	

¹⁾ Pulse test: $t \leq 300 \mu\text{s}, D \leq 2 \%$.

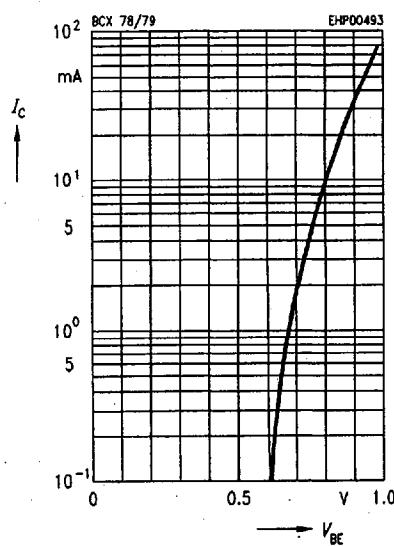
Electrical Characteristicsat $T_A = 25^\circ\text{C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC characteristics					
Transition frequency $I_c = 20 \text{ mA}, V_{CE} = 5 \text{ V}, f = 100 \text{ MHz}$	f	—	250	—	MHz
Output capacitance $V_{CB} = 10 \text{ V}, f = 1 \text{ MHz}$	C_{obo}	—	3	—	pF
	C_{ibo}	—	10	—	
Short-circuit input impedance $I_c = 2 \text{ mA}, V_{CE} = 5 \text{ V}, f = 1 \text{ kHz}$ BCX 78 VII, BCX 79 VII BCX 78 VIII, BCX 79 VIII BCX 78 IX, BCX 79 IX BCX 78 X, BCX 79 X	h_{11e}	—	2.7	—	kΩ
		—	3.6	—	
		—	4.5	—	
		—	7.5	—	
		—	—	—	
Open-circuit reverse voltage transfer ratio $I_c = 2 \text{ mA}, V_{CE} = 5 \text{ V}, f = 1 \text{ kHz}$ BCX 78 VII, BCX 79 VII BCX 78 VIII, BCX 79 VIII BCX 78 IX, BCX 79 IX BCX 78 X, BCX 79 X	h_{12e}	—	1.5	—	10^{-4}
		—	2	—	
		—	2	—	
		—	3	—	
		—	—	—	
Short-circuit forward current transfer ratio $I_c = 2 \text{ mA}, V_{CE} = 5 \text{ V}, f = 1 \text{ kHz}$ BCX 78 VII, BCX 79 VII BCX 78 VIII, BCX 79 VIII BCX 78 IX, BCX 79 IX BCX 78 X, BCX 79 X	h_{21e}	—	200	—	—
		—	260	—	
		—	330	—	
		—	520	—	
		—	—	—	
Open-circuit output admittance $I_c = 2 \text{ mA}, V_{CE} = 5 \text{ V}, f = 1 \text{ kHz}$ BCX 78 VII, BCX 79 VII BCX 78 VIII, BCX 79 VIII BCX 78 IX, BCX 79 IX BCX 78 X, BCX 79 X	h_{22e}	—	18	—	μs
		—	24	—	
		—	30	—	
		—	50	—	
		—	—	—	
Noise figure $I_c = 0.2 \text{ mA}, V_{CE} = 5 \text{ V}, R_s = 2 \text{ k}\Omega$ $f = 1 \text{ kHz}, \Delta f = 200 \text{ Hz}$	F	—	2	—	dB

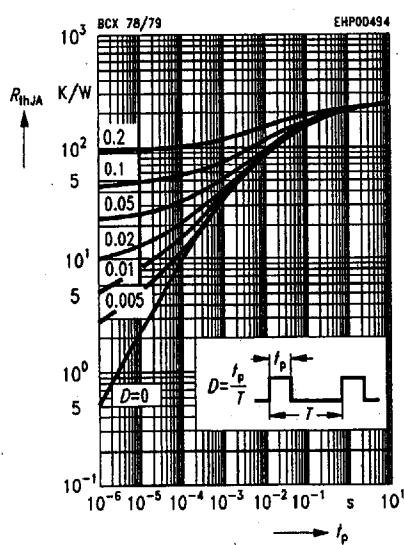
Total power dissipation $P_{\text{tot}} = f(T_A; T_C)$



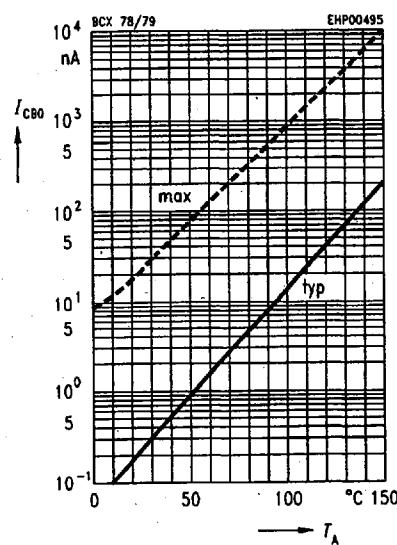
Collector current $I_C = f(V_{BE})$
 $V_{CE} = 5 \text{ V}$



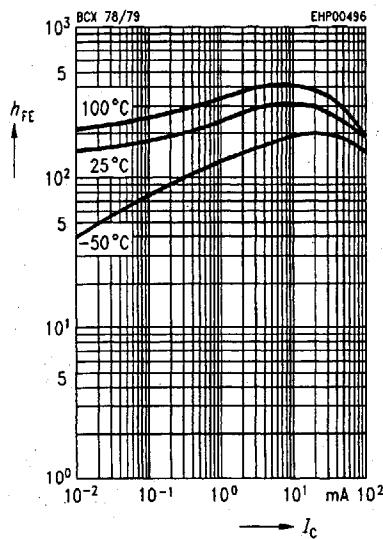
Permissible pulse load $R_{thJA} = f(t_p)$



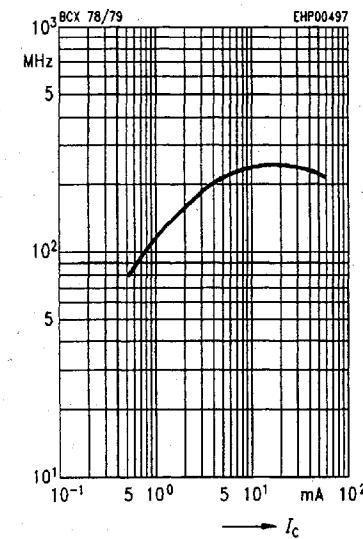
Collector cutoff current $I_{CBO} = f(T_A)$
for max. permissible reverse voltage



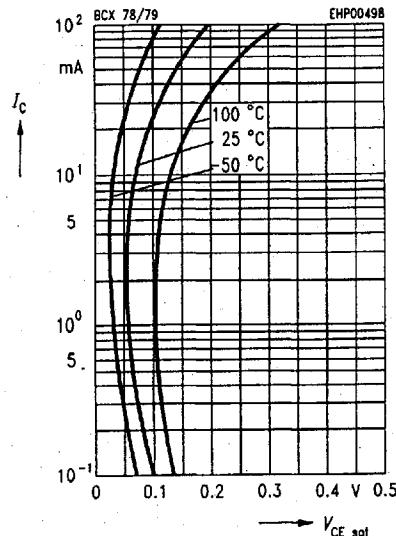
DC current gain $h_{FE} = f(I_C)$
 $V_{CE} = 5 \text{ V}$ (common emitter configuration)



Transition frequency $f_T = f(I_C)$
 $V_{CE} = 5 \text{ V}$



Collector-emitter saturation voltage
 $I_C = f(V_{CEsat})$
 $h_{FE} = 20$



Base-emitter saturation voltage
 $I_C = f(V_{BEsat})$
 $h_{FE} = 20$

